



SEMITRANS® 3

Trench IGBT Modules

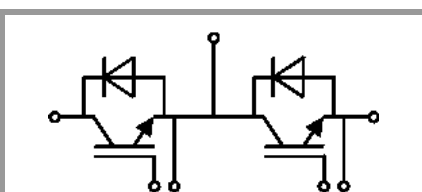
SKM300GB126D

Features

- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_C$
- UL recognized, file no. E63532

Typical Applications*

- Electronic welders
- AC inverter drives
- UPS



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Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
IGBT				
V _{CES}	T _j = 25 °C		1200	V
I _C	T _j = 150 °C	T _c = 25 °C	310	A
		T _c = 80 °C	218	A
I _{Cnom}			200	A
I _{CRM}	I _{CRM} = 2xI _{Cnom}		400	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 600 V V _{GE} ≤ 15 V V _{CES} ≤ 1200 V	T _j = 125 °C	10	µs
T _j			-40 ... 150	°C
Inverse diode				
I _F	T _j = 150 °C	T _c = 25 °C	250	A
		T _c = 80 °C	169	A
I _{Fnom}			200	A
I _{FRM}	I _{FRM} = 2xI _{Fnom}		400	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 25 °C		1656	A
T _j			-40 ... 150	°C
Module				
I _{t(RMS)}			500	A
T _{stg}			-40 ... 125	°C
V _{isol}	AC sinus 50 Hz, t = 1 min		4000	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
V _{CE(sat)}	I _C = 200 A	T _j = 25 °C		1.70	2.10	V
	V _{GE} = 15 V chipelevel	T _j = 125 °C		2.00	2.46	V
V _{CE0}	chipelevel	T _j = 25 °C		1	1.2	V
		T _j = 125 °C		0.9	1.1	V
r _{CE}	V _{GE} = 15 V chipelevel	T _j = 25 °C		3.5	4.5	mΩ
		T _j = 125 °C		5.5	6.8	mΩ
V _{GE(th)}	V _{GE} =V _{CE} , I _C = 8 mA		5	5.8	6.5	V
I _{CES}	V _{GE} = 0 V	T _j = 25 °C			2.7	mA
	V _{CE} = 1200 V	T _j = 125 °C				mA
C _{ies}	V _{CE} = 25 V V _{GE} = 0 V	f = 1 MHz		14.4		nF
C _{oes}		f = 1 MHz		0.75		nF
C _{res}		f = 1 MHz		0.65		nF
Q _G	V _{GE} = - 8 V...+ 20 V			1800		nC
R _{Gint}	T _j = 25 °C			3.8		Ω
t _{d(on)}	V _{CC} = 600 V	T _j = 125 °C		280		ns
t _r	I _C = 200 A			37		ns
E _{on}	V _{GE} = +15/-15 V			21		mJ
t _{d(off)}	R _{G on} = 1.5 Ω			560		ns
t _f	R _{G off} = 1.5 Ω			100		ns
E _{off}			T _j = 125 °C		33	
R _{th(j-c)}	per IGBT				0.12	K/W



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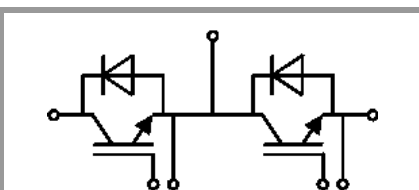
Features

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Typical Applications*

- Electronic welders
- AC inverter drives
- UPS

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
V _F = V _{EC}	I _F = 200 A	T _j = 25 °C		1.60	1.80	V
	V _{GE} = 0 V	T _j = 125 °C		1.60	1.80	V
	chiplevel					
V _{F0}	chiplevel	T _j = 25 °C		1	1.1	V
		T _j = 125 °C		0.8	0.9	V
r _F	chiplevel	T _j = 25 °C		3	3.5	mΩ
		T _j = 125 °C		4	4.5	mΩ
I _{RRM}	I _F = 200 A	T _j = 125 °C		290		A
Q _{rr}	di/dt _{off} = 6200 A/μs	T _j = 125 °C		44		μC
E _{rr}	V _{GE} = -15 V	T _j = 125 °C		18		mJ
	V _{CC} = 600 V					
R _{th(j-c)}	per diode				0.25	K/W
Module						
L _{CE}				15		nH
R _{CC'+EE'}	terminal-chip	T _C = 25 °C		0.35		mΩ
		T _C = 125 °C		0.5		mΩ
R _{th(c-s)}	per module			0.02	0.038	K/W
M _s	to heat sink M6		3		5	Nm
M _t		to terminals M6	2.5		5	Nm
						Nm
w					325	g



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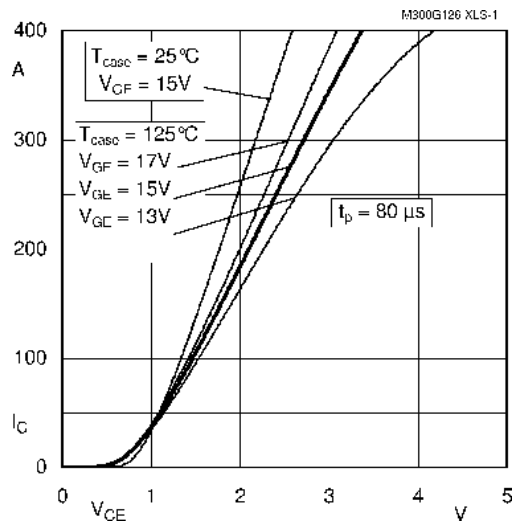


Fig. 1: Typ. output characteristic, inclusive $R_{CC} + E_{E'}$

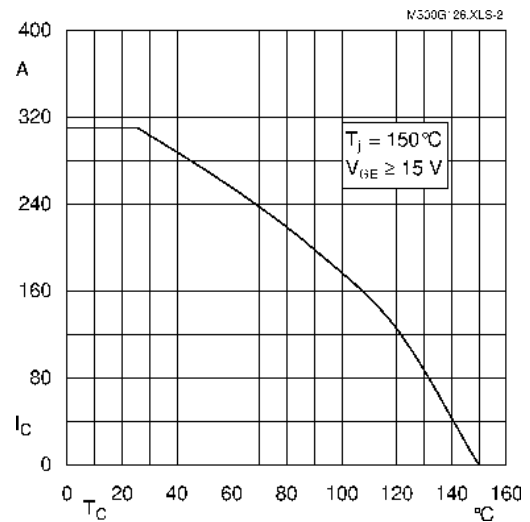


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

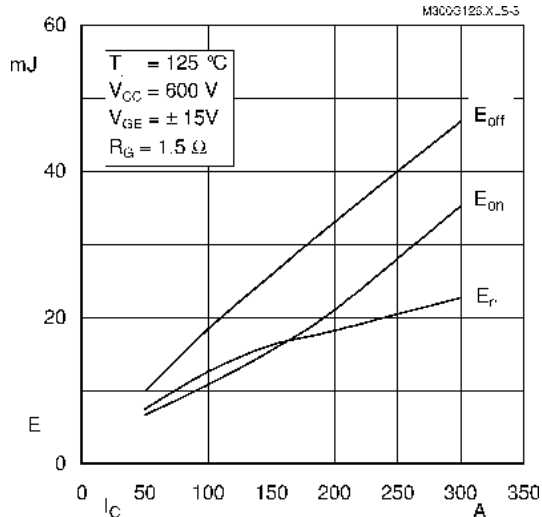


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

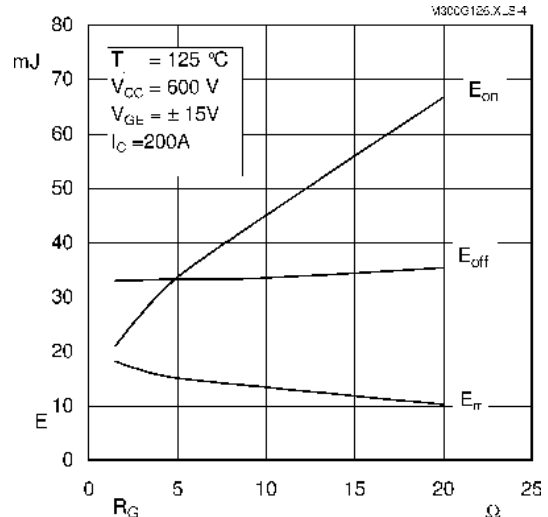


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

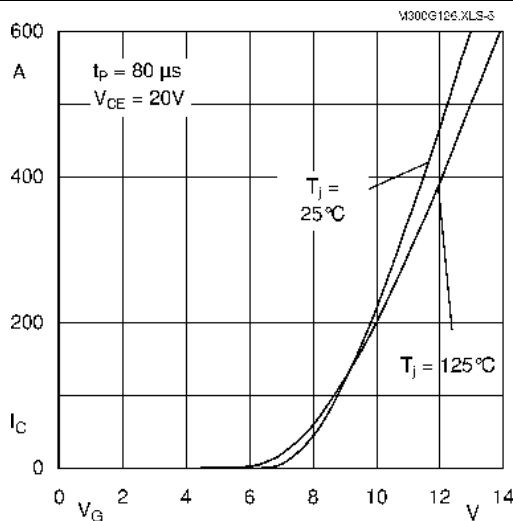


Fig. 5: Typ. transfer characteristic

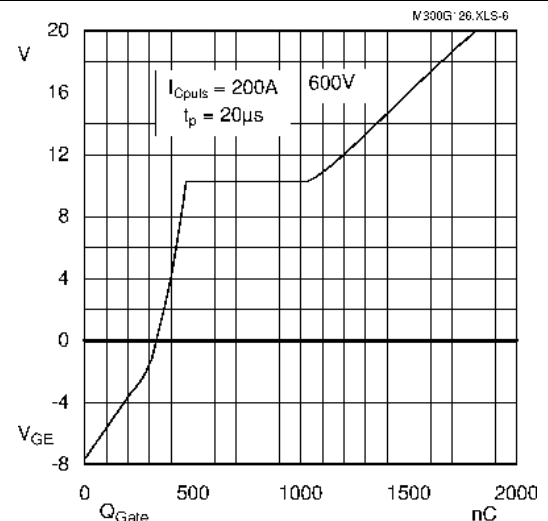
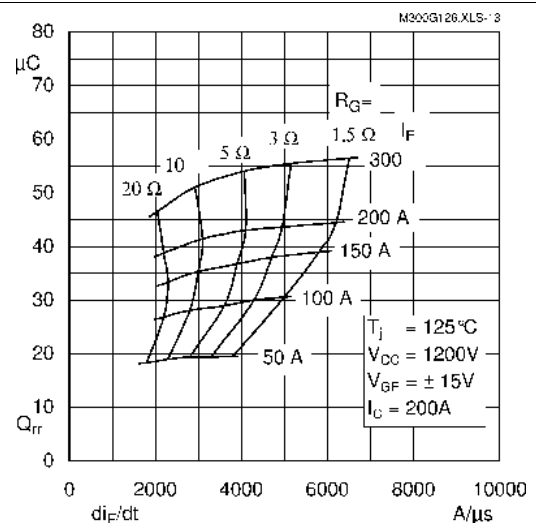
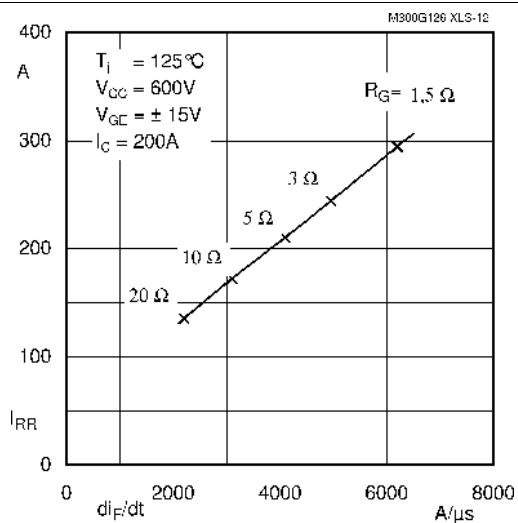
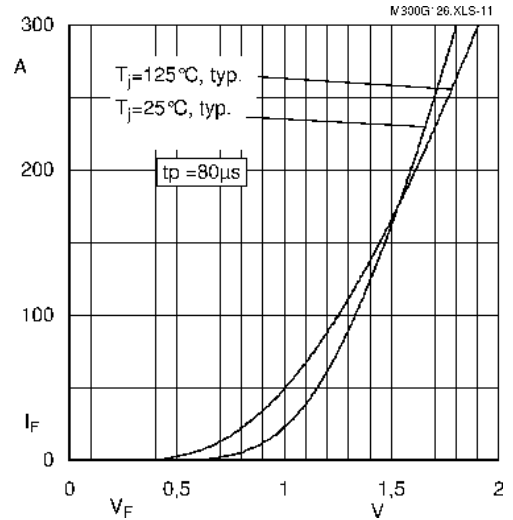
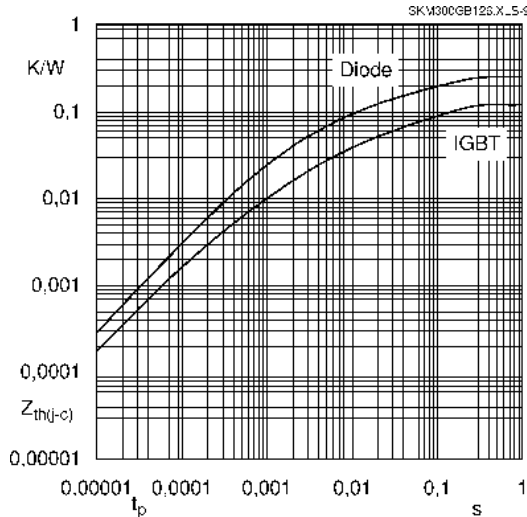
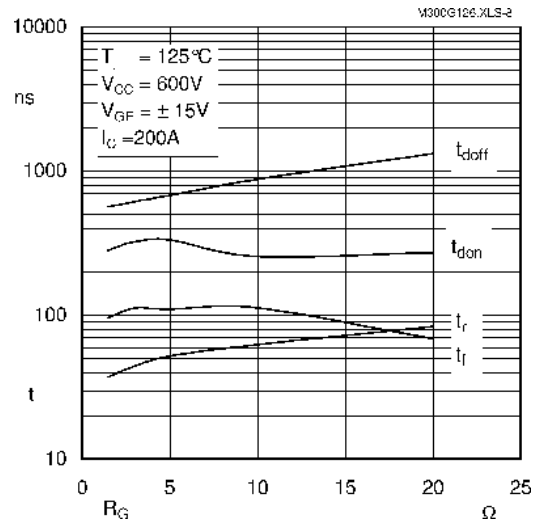
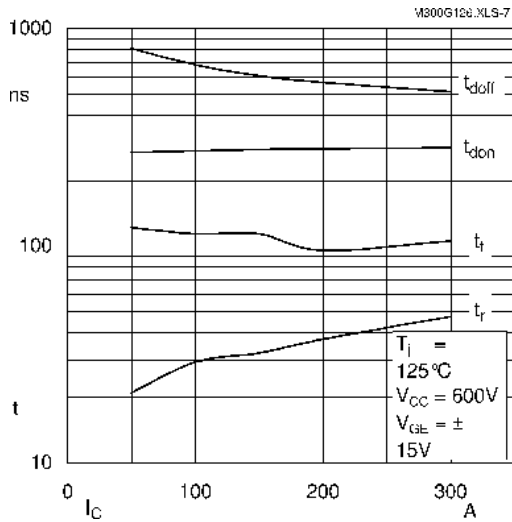
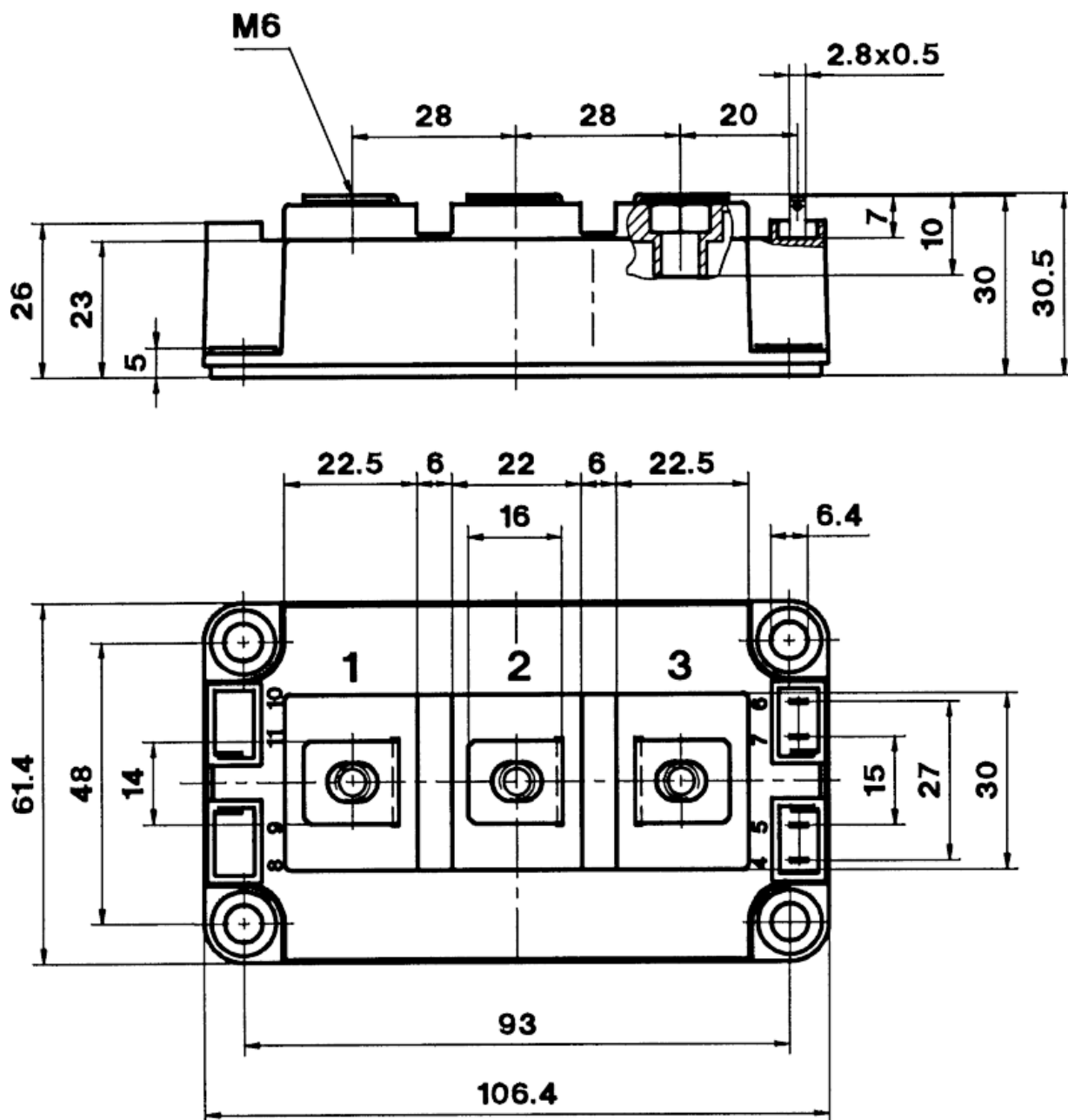


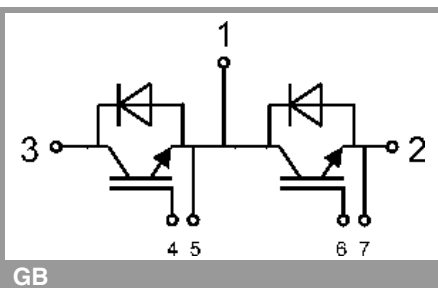
Fig. 6: Typ. gate charge characteristic



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.